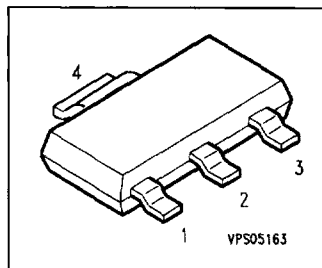


**NPN Silicon RF Transistor**

- For low noise, low distortion broadband amplifiers in antenna and telecommunications systems up to 1.5GHz at collector currents from 20mA to 80mA
- Power amplifier for DECT and PCN systems
- $f_T = 7.5\text{GHz}$   
 $F = 1.5\text{ dB at } 900\text{MHz}$



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Ordering Code	Pin Configuration				Package
BFG 196	BFG196	Q62702-F1292	1 = E	2 = B	3 = E	4 = C	SOT-223

**Maximum Ratings**

Parameter	Symbol	Values	Unit
Collector-emitter voltage	$V_{CEO}$	12	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2	
Collector current	$I_C$	100	mA
Base current	$I_B$	12	
Total power dissipation $T_S \leq 90\text{ }^\circ\text{C}$	$P_{tot}$	800	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Ambient temperature	$T_A$	- 65 ... + 150	
Storage temperature	$T_{stg}$	- 65 ... + 150	

**Thermal Resistance**

Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 75$	K/W
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1)  $T_S$  is measured on the collector lead at the soldering point to the pcb.

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	1	$\mu\text{A}$
DC current gain $I_C = 50 \text{ mA}, V_{CE} = 8 \text{ V}$	$h_{FE}$	50	100	200	-

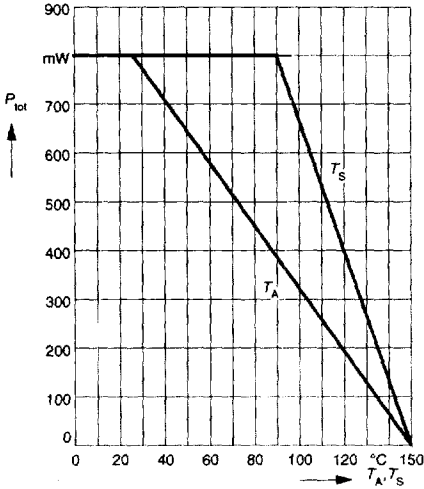
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$	$f_T$	5	7.5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	0.97	1.4	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ce}$	-	0.4	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{eb}$	-	4	-	
Noise figure $I_C = 20\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$F$	-	1.5 2.5	-	dB
Power gain <sup>2)</sup> $I_C = 50\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ $Z_L = Z_{Lopt}$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$G_{ma}$	-	14 8.5	-	
Transducer gain $I_C = 50\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	11.5 6	-	

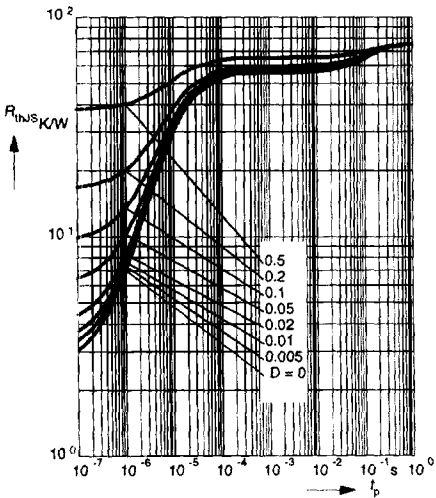
$$2) G_{ma} = |S_{21}/S_{12}| (k - (k^2 - 1)^{1/2})$$

**Total power dissipation  $P_{tot} = f(T_A^*, T_S)$**

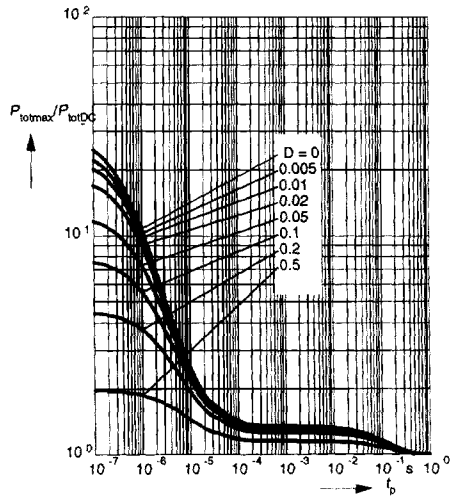
\* Package mounted on epoxy



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**

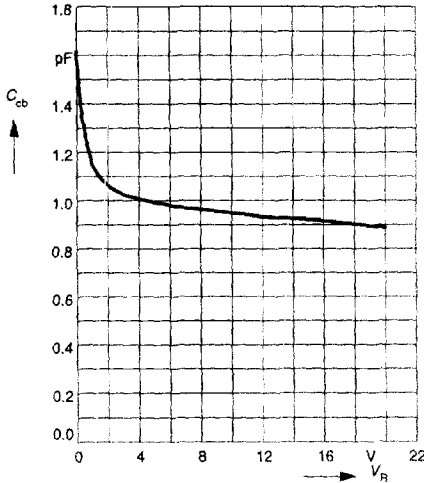


**Permissible Pulse Load  $P_{totmax}/P_{totDC} = f(t_p)$**



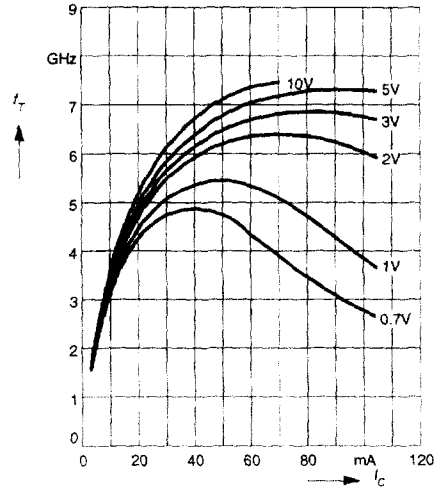
**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

$V_{BE} = v_{be} = 0, f = 1\text{MHz}$



**Transition frequency  $f_T = f(I_C)$**

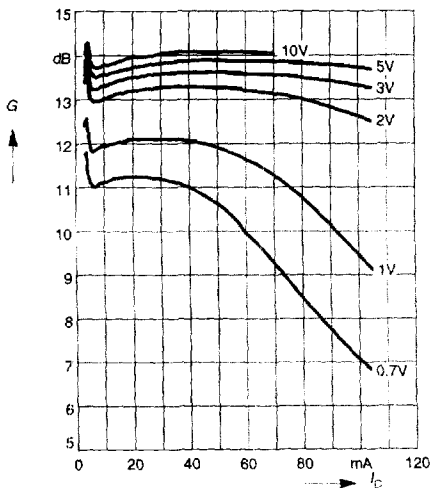
$V_{CE} = \text{Parameter}$



**Power Gain  $G_{ma}, G_{ms} = f(I_C)$**

$f = 0.9\text{GHz}$

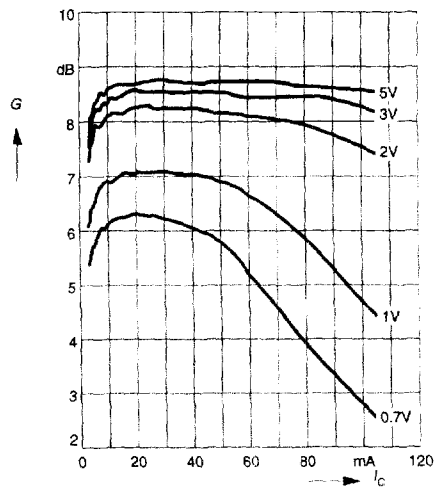
$V_{CE} = \text{Parameter}$



**Power Gain  $G_{ma}, G_{ms} = f(I_C)$**

$f = 1.8\text{GHz}$

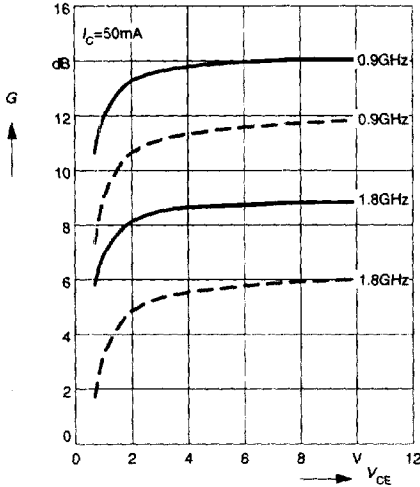
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(V_{CE})$ : \_\_\_\_\_

$|S_{21}|^2 = f(V_{CE})$ : - - - - -

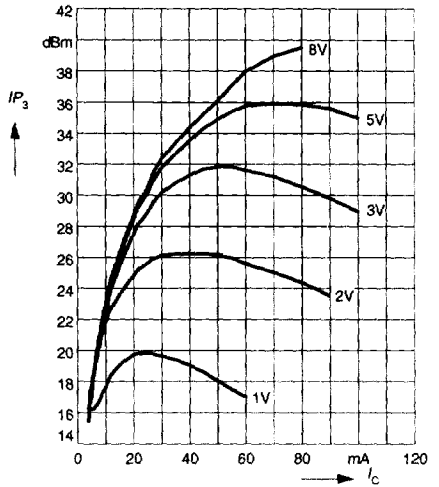
$f =$  Parameter



**Intermodulation Intercept Point**  $IP_3 = f(I_C)$

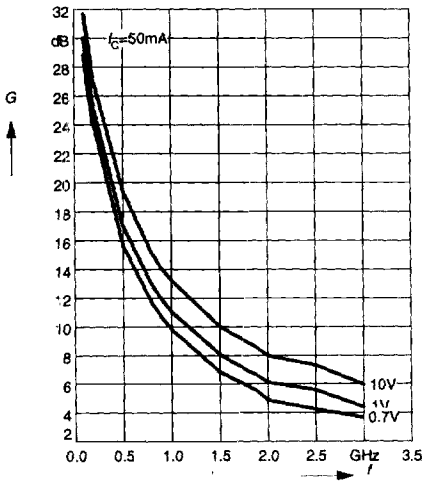
(3rd order, Output,  $Z_S = Z_L = 50\Omega$ )

$V_{CE} =$  Parameter,  $f = 900\text{MHz}$



**Power Gain**  $G_{ma}, G_{ms} = f(f)$

$V_{CE} =$  Parameter



**Power Gain**  $|S_{21}|^2 = f(f)$

$V_{CE} =$  Parameter

